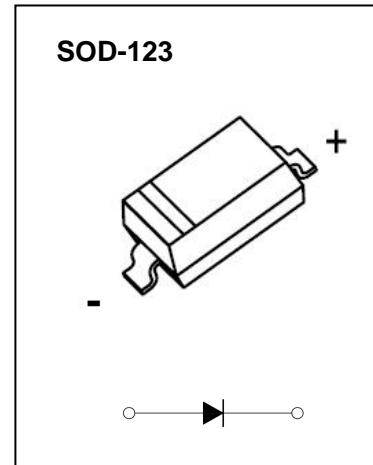




Schottky Barrier Diode

**FEATURES**

- Low Forward Voltage Drop
- Guard Ring Construction for Transient Protection
- Negligible Reverse Recovery Time
- Low Capacitance



**MARKING:**

SD103AW:S4	SD103BW:S5	SD103CW:S6
- S4 +	- S5 +	- S6 +
- S4 +	- S5 +	- S6 +

The marking bar indicates the cathode  
Solid dot = Green molding compound device, if none,  
the normal device.

**MAXIMUM RATINGS (  $T_a=25^\circ\text{C}$  unless otherwise noted )**

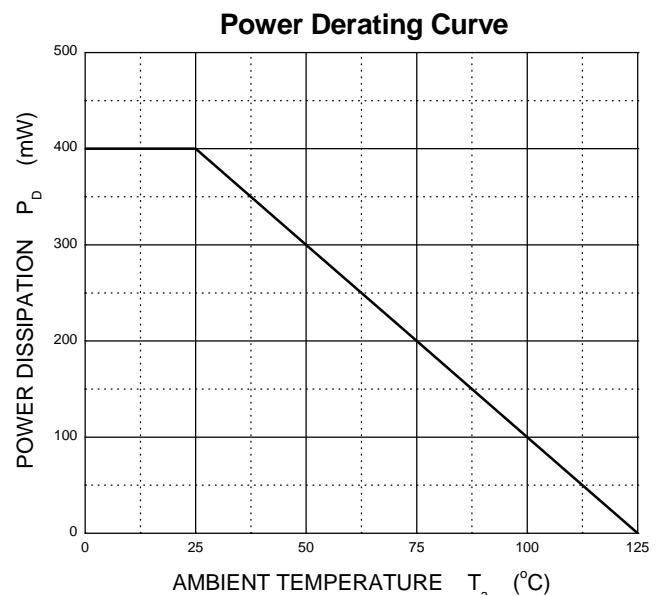
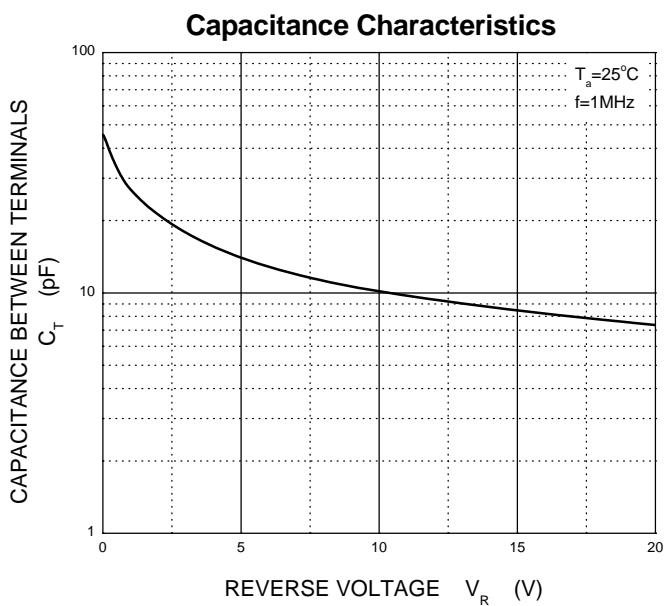
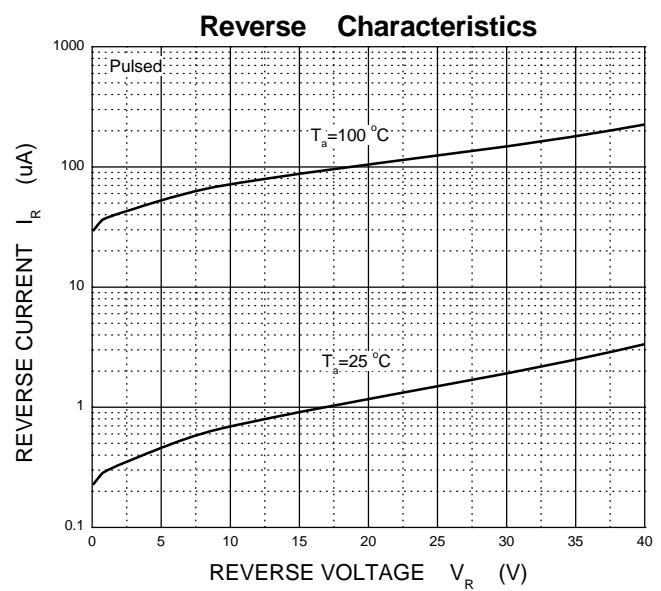
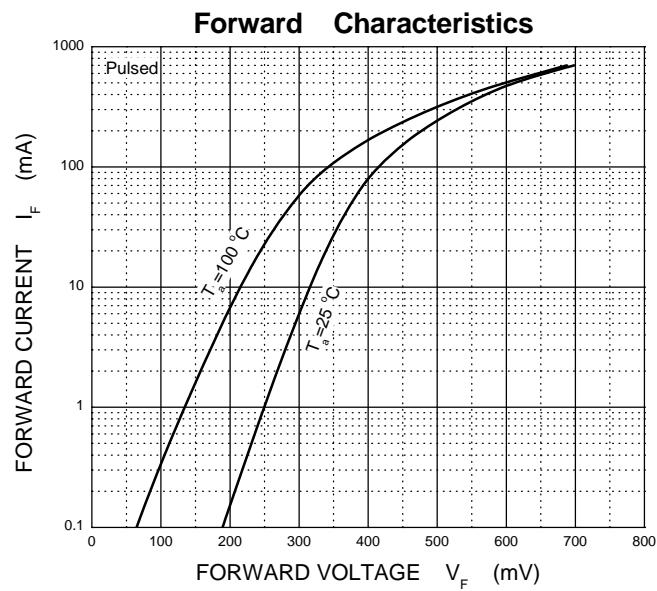
Symbol	Parameter	Value			Unit
		SD103AW	SD103BW	SD103CW	
$V_{RRM}$	Peak Repetitive Reverse Voltage	40	30	20	V
$V_{RWM}$	Working Peak Reverse Voltage				
$V_{R(\text{RMS})}$	RMS Reverse Voltage	28	21	14	V
$I_{FM}$	Forward Continuous Current	350			mA
$I_{FSM}$	Non-repetitive Peak Forward Surge Current@ $t=8.3\text{ms}$	2			A
$P_D$	Power Dissipation	400			mW
$R_{\theta JA}$	Thermal Resistance from Junction to Ambient	250			$^\circ\text{C}/\text{W}$
$T_j$	Junction Temperature	125			$^\circ\text{C}$
$T_{stg}$	Storage Temperature	-55~+150			$^\circ\text{C}$

**ELECTRICAL CHARACTERISTICS( $T_a=25^\circ\text{C}$  unless otherwise specified)**

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Reverse voltage	$V_{(BR)}$	$I_R=100\mu\text{A}$	SD103AW	40		
			SD103BW	30		
			SD103CW	20		
Reverse current	$I_R$	$V_R=30\text{V}$	SD103AW			5
		$V_R=20\text{V}$	SD103BW			
		$V_R=10\text{V}$	SD103CW			
Forward voltage	$V_F$	$I_F=20\text{mA}$			0.37	V
		$I_F=200\text{mA}$			0.6	
Total capacitance	$C_{tot}$	$V_R=0\text{V}, f=1\text{MHz}$		50		pF
Reverse recovery time	$t_{rr}$	$I_F=I_R=200\text{mA}, I_{rr}=0.1 \times I_R, R_L=100\Omega$		10		ns

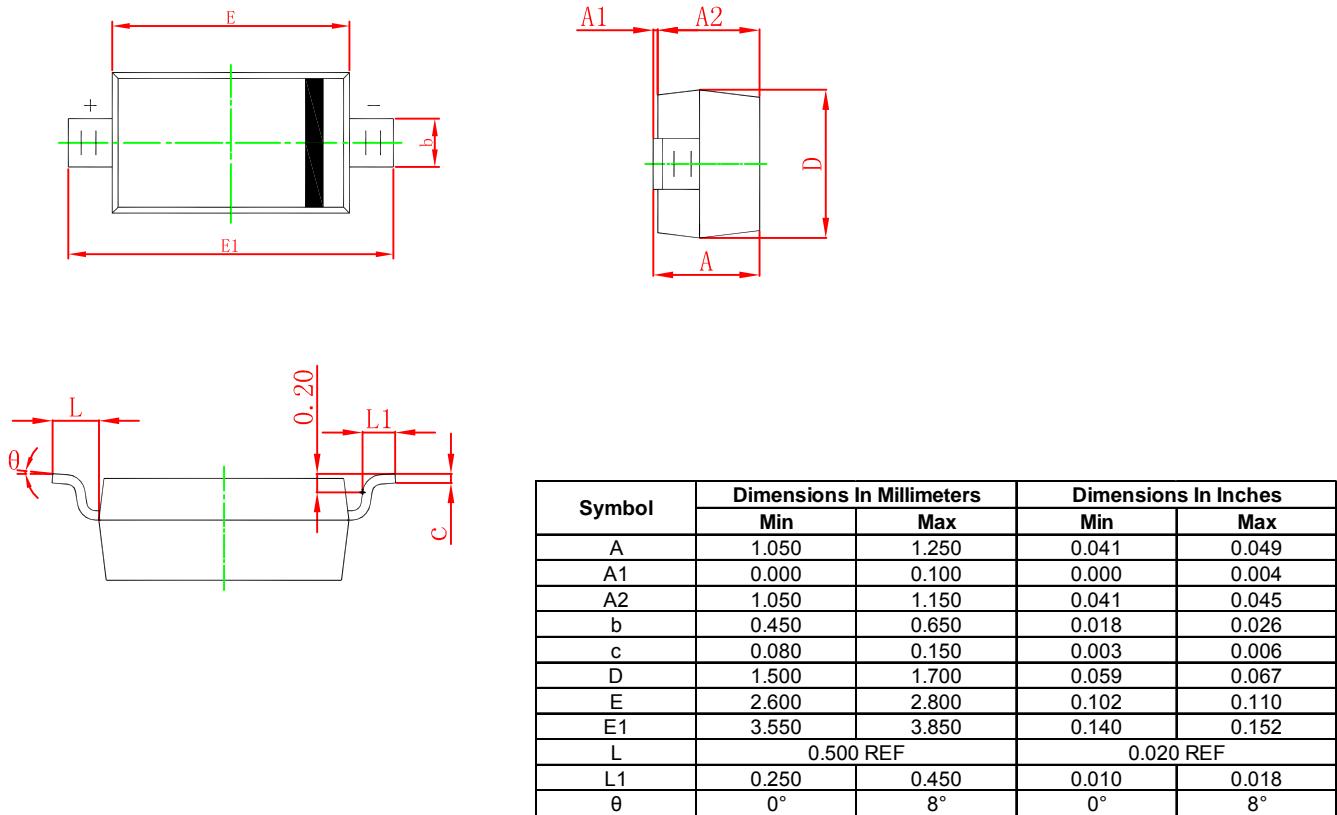


### Typical Characteristics

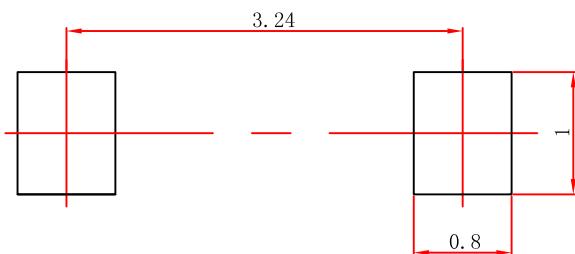




### SOD-123 Package Outline Dimensions



### SOD-123 Suggested Pad Layout



**Note:**

1. Controlling dimension:in millimeters.
- 2.General tolerance: $\pm 0.05\text{mm}$ .
- 3.The pad layout is for reference purposes only.